

Amendments to the Specification:

**Paragraph at page 9, line 18 to page 10, line 5:**

Using an inverted wafer orientation in an RTP reactor for the most part designed for conventional upwardly facing orientation presents some difficulties with wafer handling. As mentioned above, the wafer 12 should be supported on its periphery only within its edge exclusion zone 52. Transferring the wafer into and out of reactor requires further modifications. The lift pins 22 in a conventional RTP reactor 10 typically contact the back side of the wafer 12 at positions underlying production [[die]] dies. Such contact in the inventive reactor 60 with the die will most likely introduce sufficient damage to the contacted die to render the die inoperable. Such damage could be accepted as trading off yield of a limited number of [[die]] dies. The die areas may even be left unimaged. However, this approach is disfavored since yield is not readily surrendered. Further, to minimize yield loss for such RTP processing on multiple levels, it becomes important to rigidly maintain the orientation of the wafer patterning relative to the lift pin locations. Another approach moves the lift pins to areas of the structured dye regions, which do not yield useful die in any case. This solution has its own disadvantages. First, it again requires careful orientation of the wafer patterning relative to the lift pin locations. Secondly, different integrated circuit designs likely have different die sizes and ratio of length to width. As a result, the structured dye areas may vary from one IC design to another. Accordingly, it may be necessary to move the locations of the lift pins when processing a different IC design. Although feasible; this design specific location of lift pins is feasible, it is [[but]] economically disadvantageous.